

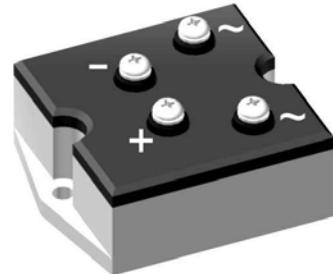
Standard Rectifier Module

1~ Rectifier
$V_{RRM} = 1600 \text{ V}$
$I_{DAV} = 45 \text{ A}$
$I_{FSM} = 750 \text{ A}$

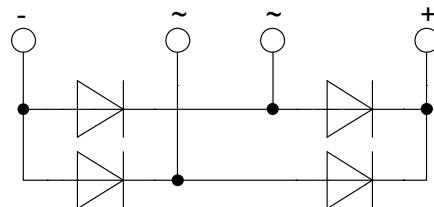
1~ Rectifier Bridge

Part number

VBO50-16NO7



E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For one phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

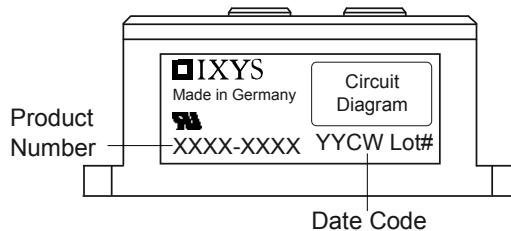
Package: PWS-B

- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Aluminium internally DCB isolated
- Advanced power cycling

Rectifier

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1700	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1600	V
I_R	reverse current	$V_R = 1600 V$ $V_R = 1600 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		100 1.5	μA mA
V_F	forward voltage drop	$I_F = 20 A$ $I_F = 40 A$ $I_F = 20 A$ $I_F = 40 A$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		1.03 1.14 0.92 1.06	V V
I_{DAV}	bridge output current	$T_C = 85^\circ C$ rectangular $d = 0.5$	$T_{VJ} = 150^\circ C$		45	A
V_{FO} r_F	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 150^\circ C$		0.76 6.9	V $m\Omega$
R_{thJC}	thermal resistance junction to case				2.7	K/W
R_{thCH}	thermal resistance case to heatsink				0.4	K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		46	W
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$ $V_R = 0 V$ $T_{VJ} = 150^\circ C$ $V_R = 0 V$		750 810 640 690	A
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$ $V_R = 0 V$ $T_{VJ} = 150^\circ C$ $V_R = 0 V$		2.82 2.73 2.05 1.98	kA ² s kA ² s kA ² s kA ² s
C_J	junction capacitance	$V_R = 400 V; f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$		10	pF

Package PWS-B		Ratings			
Symbol	Definition	Conditions	min.	typ.	max.
					Unit
I_{RMS}	RMS current	per terminal			100 A
T_{stg}	storage temperature		-40		125 °C
T_{vJ}	virtual junction temperature		-40		150 °C
Weight				193	g
M_D	mounting torque		4.25		5.75 Nm
M_T	terminal torque		2.5		3.5 Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	11.0		mm
$d_{Spb/Abp}$		terminal to backside	7.5		mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3000 2500		V V

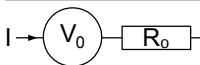


Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VBO50-16NO7	VBO50-16NO7	Box	10	472271

Equivalent Circuits for Simulation

* on die level

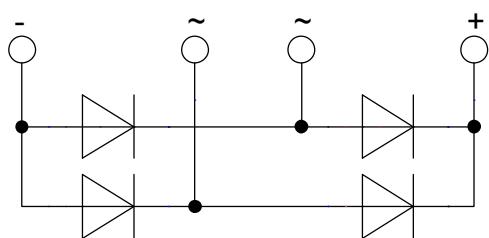
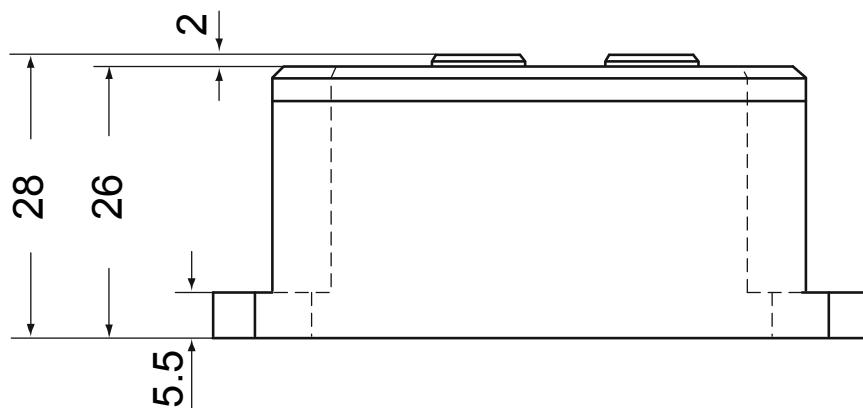
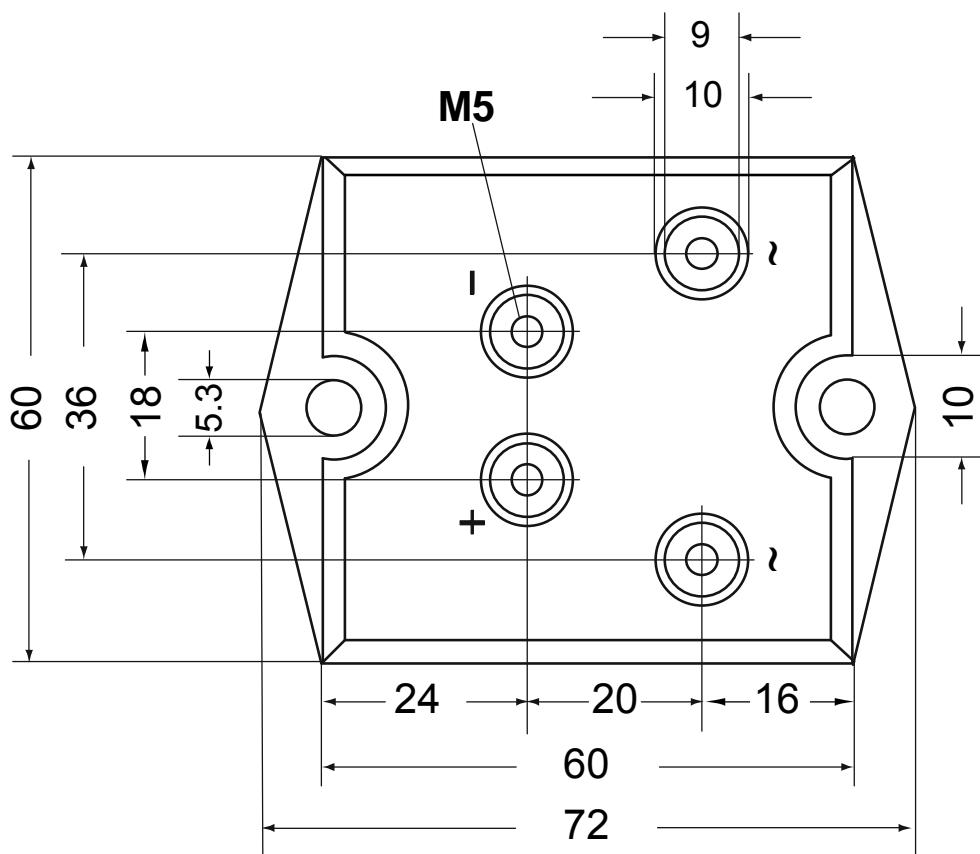
$T_{vJ} = 150$ °C



Rectifier

$V_{0\max}$ threshold voltage 0.76 V
 $R_{0\max}$ slope resistance * 5.7 mΩ

Outlines PWS-B



Rectifier

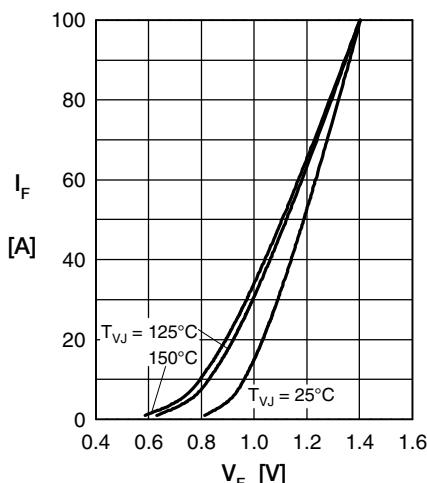


Fig. 1 Forward current vs. voltage drop per diode

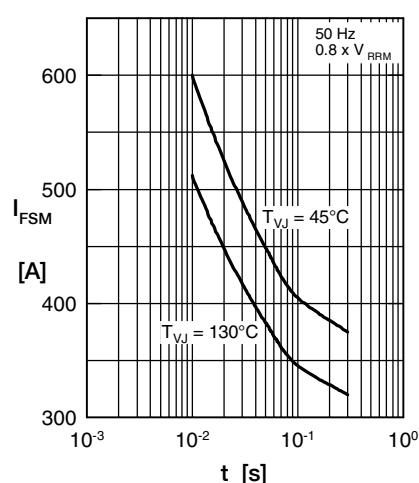


Fig. 2 Surge overload current vs. time per diode

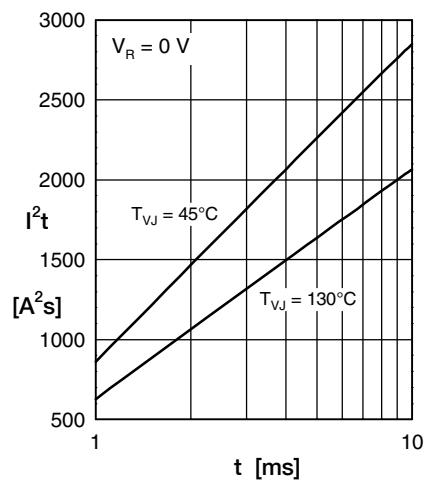
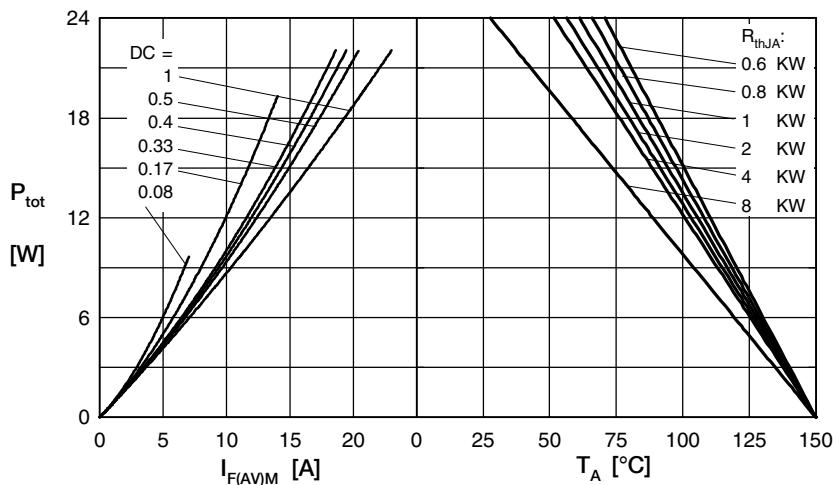
Fig. 3 I^2t vs. time per diode

Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

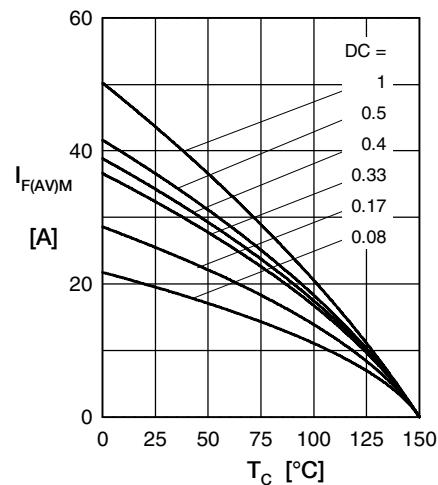


Fig. 5 Max. forward current vs. case temperature per diode

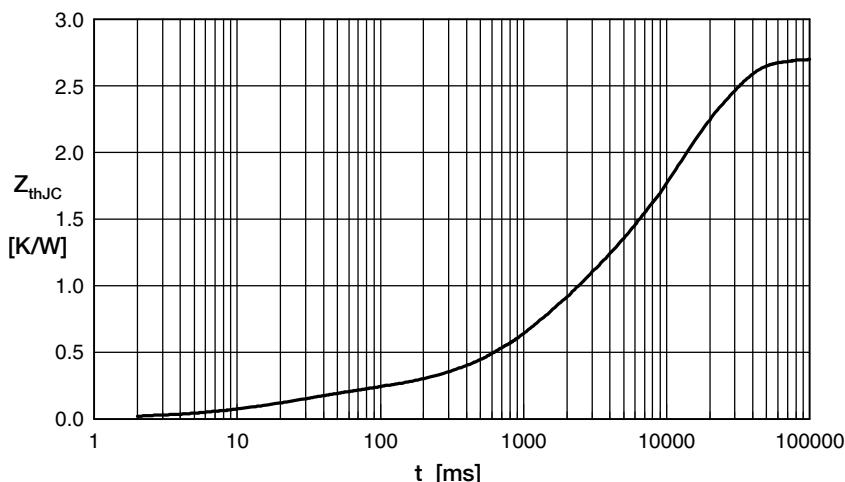


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.040	0.010
2	0.150	0.030
3	0.610	1.350
4	1.900	14.00